



ADVANCED TECHNOLOGY (TAIWAN) CORP

台灣科技股份有限公司

No. 1, Industry E, Road VI,
Science-Based Industrial Park.
Hsin-Chu, Taiwan, R. O. C.

新竹市科學工業園區工業東六路一號

TEL: 035-777300

FAX: 035-776464

T-41-19

AT010AR

I、Scope:

The specification applies to GaAsP on GaAs red LED chip,
Device No. AT010AR

II、Structure:

- * GaAsP on GaAs red LED chip
- * P/N mesa type
- * Electrode: P-face (anode) side: Aluminum
N-face (cathode) side: Gold alloy

III、Size:

- * Chip size : 280 μ m $\times$ 280 μ m (11mil $\times$ 11mil)
- * Emission area : 250 μ m $\times$ 250 μ m (10mil $\times$ 10mil)
- * Refer to drawing on back page: AR-1

IV、Electro-optical Characteristics:

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V _f	I _f = 10mA		1.70	1.90	V
Reverse Current	I _r	V _r = 5V			10	μ A
Luminous Intensity	I _v	I _f = 10mA	300			μ cd
Peak Emission Wavelength	λ_p	I _f = 10mA		660		nm
Spectrum Half-Width	$\Delta \lambda$	I _f = 10mA		20		nm

(Ta = +25°C)

**ADVANCED TECHNOLOGY (TAIWAN) CORP**

台灣科技股份有限公司

No. 1, Industry E. Road VI,
Science-Based Industrial Park.
Hsin-Chu, Taiwan, R. O. C.

新竹市科學工業園區工業東六路一號

TEL: 035-777300

FAX: 035-776464

T-41-19

Fig.: AR-1 Pattern Drawing

Unit : μm
Scale: 200/1